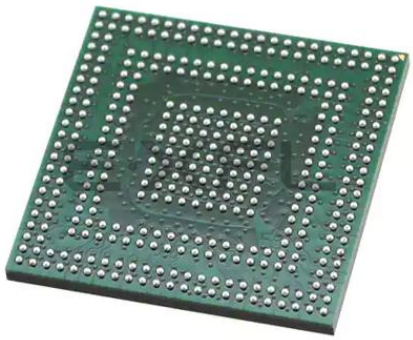

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	369-LFBGA
Supplier Device Package	369-PBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/ppc8306svmaddca

  - Two TDM interfaces supporting up to 128 QUICC multichannel controller channels, each running at 64 kbps

For more information on QUICC Engine sub-modules, see *QUICC Engine Block Reference Manual with Protocol Interworking*.

- DDR SDRAM memory controller
  - Programmable timing supporting DDR2 SDRAM
  - Integrated SDRAM clock generation
  - 16-bit data interface, up to 266-MHz data rate
  - 14 address lines
  - The following SDRAM configurations are supported:
    - Up to two physical banks (chip selects), 256-Mbyte per chip select for 16 bit data interface.
    - 64-Mbit to 2-Gbit devices with x8/x16 data ports (no direct x4 support)
    - One 16-bit device or two 8-bit devices on a 16-bit bus,
  - Support for up to 16 simultaneous open pages for DDR2
  - One clock pair to support up to 4 DRAM devices
  - Supports auto refresh
  - On-the-fly power management using CKE
- Enhanced local bus controller (eLBC)
  - Multiplexed 26-bit address and 8-/16-bit data operating at up to 66 MHz
  - Eight chip selects supporting eight external slaves
    - Four chip selects dedicated
    - Four chip selects offered as multiplexed option
  - Supports boot from parallel NOR Flash and parallel NAND Flash
  - Supports programmable clock ratio dividers
  - Up to eight-beat burst transfers
  - 16- and 8-bit ports, separate $\overline{\text{LWE}}$ for each 8 bit
  - Three protocol engines available on a per chip select basis:
    - General-purpose chip select machine (GPCM)
    - Three user programmable machines (UPMs)
    - NAND Flash control machine (FCM)
  - Variable memory block sizes for FCM, GPCM, and UPM mode
  - Default boot ROM chip select with configurable bus width (8 or 16)
  - Provides two Write Enable signals to allow single byte write access to external 16-bit eLBC slave devices
- Integrated programmable interrupt controller (IPIC)
  - Functional and programming compatibility with the MPC8260 interrupt controller
  - Support for external and internal discrete interrupt sources
  - Programmable highest priority request

  - The power management controller detects that the system is not idle and there are outstanding transactions on the internal bus or an external interrupt.
- Parallel I/O
  - General-purpose I/O (GPIO)
    - 56 parallel I/O pins multiplexed on various chip interfaces
    - Interrupt capability
- System timers
  - Periodic interrupt timer
  - Software watchdog timer
  - Eight general-purpose timers
- Real time clock (RTC) module
  - Maintains a one-second count, unique over a period of thousands of years
  - Two possible clock sources:
    - External RTC clock (RTC_PIT_CLK)
    - CSB bus clock
- IEEE Std. 1149.1™ compliant JTAG boundary scan

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8306S. The MPC8306S is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

The following table provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic	Symbol	Max Value	Unit	Notes
Core supply voltage	V_{DD}	–0.3 to 1.26	V	—
PLL supply voltage	AV_{DD1} AV_{DD2} AV_{DD3}	–0.3 to 1.26	V	—
DDR2 DRAM I/O voltage	GV_{DD}	–0.3 to 1.98	V	—
Local bus, DUART, system control and power management, I^2C, SPI, MII, RMII, MII management, USB and JTAG I/O voltage	OV_{DD}	–0.3 to 3.6	V	2

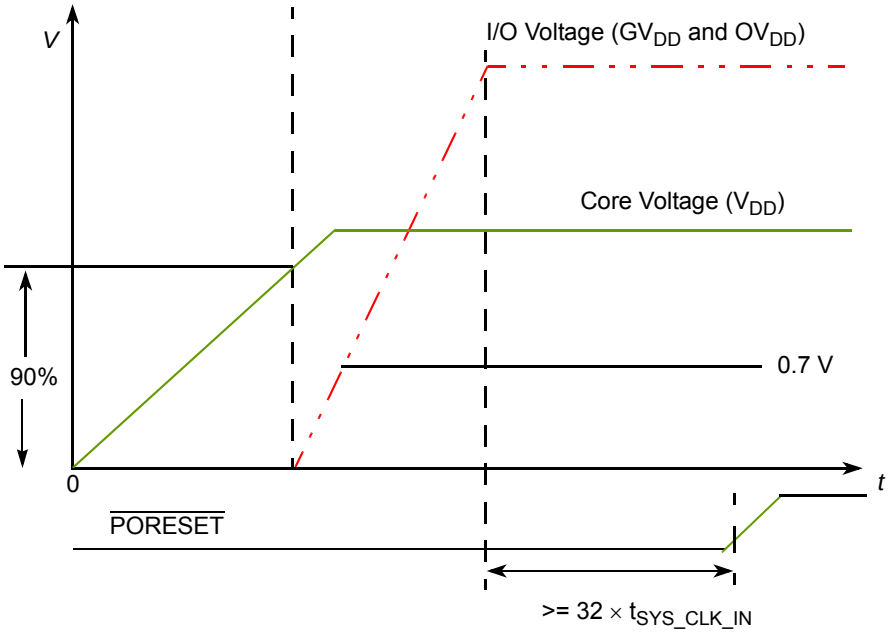


Figure 3. MPC8306S Power-Up Sequencing Example

3 Power Characteristics

The typical power dissipation for this family of MPC8306S devices is shown in the following table.

Table 5. MPC8306S Power Dissipation

Core Frequency (MHz)	QUICC Engine Frequency (MHz)	CSB Frequency (MHz)	Typical	Maximum	Unit	Note
133	133	133	0.272	0.618	W	1, 2, 3
200	233	133	0.291	0.631	W	1, 2, 3
266	233	133	0.451	0.925	W	1, 2, 3
333	233	133	0.471	0.950	W	1, 2, 3

Notes:

1. The values do not include I/O supply power (OV_{DD} and GV_{DD}), but it does include V_{DD} and AV_{DD} power. For I/O power values, see Table 6.
2. Typical power is based on a nominal voltage of V_{DD} = 1.0 V, ambient temperature, and the core running a Dhrystone benchmark application. The measurements were taken on the evaluation board using WC process silicon.
3. Maximum power is based on a voltage of V_{DD} = 1.05 V, WC process, a junction T_J = 105°C, and a smoke test code.

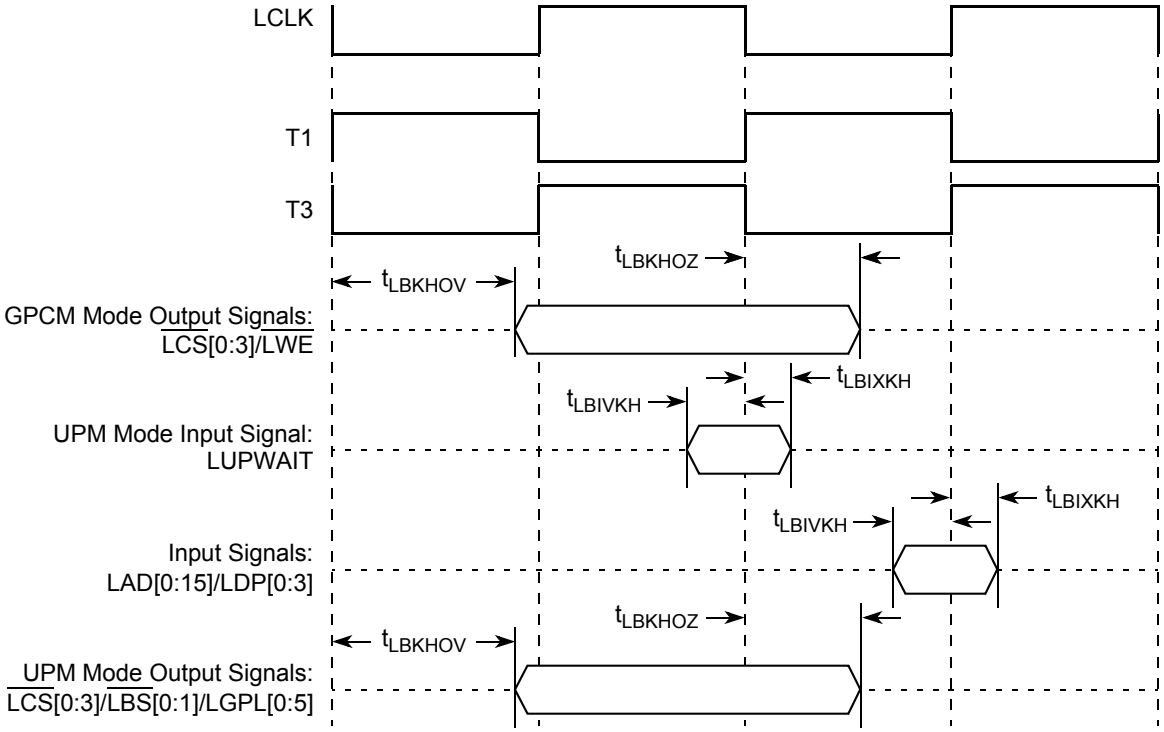


Figure 9. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2

The following figure shows the RMII receive AC timing diagram.

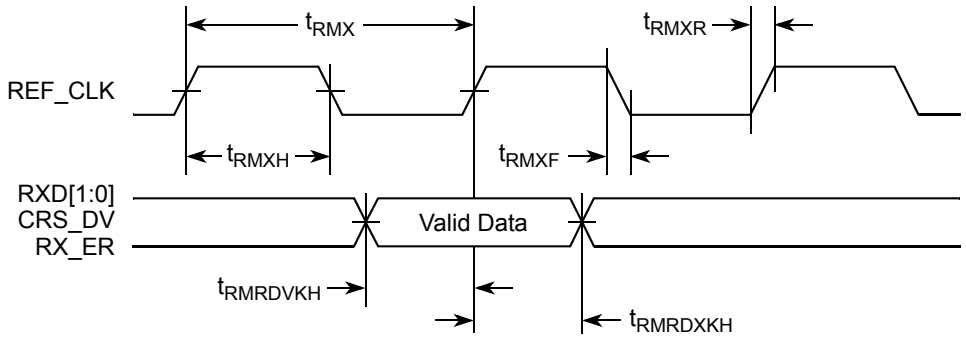


Figure 16. RMII Receive AC Timing Diagram

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for MII, and RMII are specified in Section 8.1, "Ethernet Controller (10/100 Mbps)—MII/RMII Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in the following table.

Table 24. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	—		3	3.6	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	OV_{DD} = Min	2.40	OV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	OV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$		—	±5	μA

8.3.2 MII Management AC Electrical Specifications

The following table provides the MII management AC timing specifications.

Table 25. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V ± 300mV.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit	Note
MDC frequency	f_{MDC}	—	2.5	—	MHz	—
MDC period	t_{MDC}	—	400	—	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—

Table 25. MII Management AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} is 3.3 V ± 300mV.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit	Note
MDC to MDIO delay	t_{MDKHDX}	10	—	70	ns	—
MDIO to MDC setup time	t_{MDDVKH}	8.5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	—
MDC fall time	t_{MDHF}	—	—	10	ns	—

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

The following figure shows the MII management AC timing diagram.

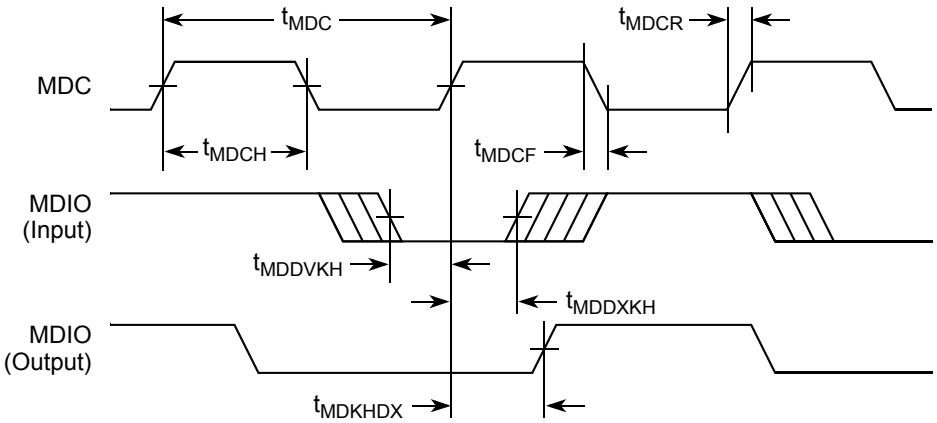


Figure 17. MII Management Interface Timing Diagram

Table 29. HDLC AC Timing Specifications[1] (continued)

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	9	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	0	—	ns
Inputs—External clock input hold time	t_{HEIXKH}	1	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of QE_CLK_IN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

The following figure provides the AC test load.

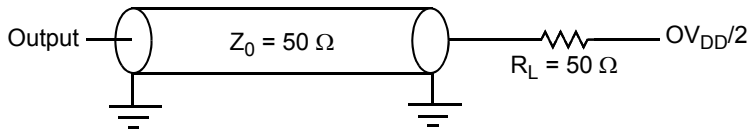
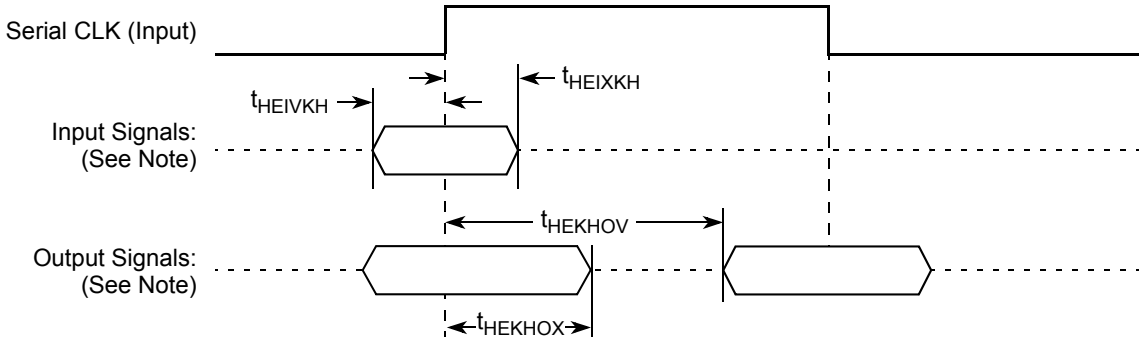


Figure 20. AC Test Load

Figure 21 and Figure 22 represent the AC timing from Table 29. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

The following figure shows the timing with external clock.



Note: The clock edge is selectable.

Figure 21. AC Timing (External Clock) Diagram

13 I²C

This section describes the DC and AC electrical characteristics for the I²C interface of the MPC8306S.

13.1 I²C DC Electrical Characteristics

The following table provides the DC electrical characteristics for the I²C interface of the MPC8306S.

Table 34. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 300mV.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	0.4	V	1
Output fall time from V_{IH}(min) to V_{IL}(max) with a bus capacitance from 10 to 400 pF	t_{I2KLKV}	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	3
Capacitance for each I/O pin	C_I	—	10	pF	—
Input current ($0 V \le V_{IN} \le OV_{DD}$)	I_{IN}	—	±5	μA	4

Notes:
1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8306S PowerQUICC II Pro Integrated Communications Processor Family Reference Manual* for information on the digital filter used.
4. I/O pins obstructs the SDA and SCL lines if OV_{DD} is switched off.

13.2 I²C AC Electrical Specifications

The following table provides the AC timing parameters for the I²C interface of the MPC8306S.

Table 35. I²C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 34).

Parameter	Symbol[1]	Min	Max	Unit
SCL clock frequency	f_{I2C}	0	400	kHz
Low period of the SCL clock	t_{I2CL}	1.3	—	μs
High period of the SCL clock	t_{I2CH}	0.6	—	μs
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs
Data setup time	t_{I2DVKH}	100	—	ns
Data hold time: I²C bus devices	t_{I2DXKL}	300	0.9[3]	μs
Rise time of both SDA and SCL signals	t_{I2CR}	$20 + 0.1\ C_B$[4]	300	ns

Table 42. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$	—	±5	μA

17.2 SPI AC Timing Specifications

The following table and provide the SPI input and output AC timing specifications.

Table 43. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOV}	0.5	6	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOV}	2	8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	6	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of SPICLK to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).
3. All units of output delay must be enabled for 8306S output port spimosi (SPI Master Mode)
4. delay units must not be enabled for Slave Mode.

The following figure provides the AC test load for the SPI.

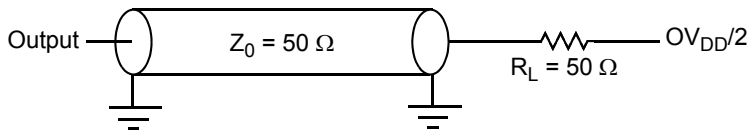


Figure 29. SPI AC Test Load

Figure 30 and Figure 31 represent the AC timing from Table 43. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Table 44. JTAG Interface DC Electrical Characteristics (continued)

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$	—	±5	μA

18.2 JTAG AC Electrical Characteristics

This section describes the AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8306S. The following table provides the JTAG AC timing specifications as defined in Figure 33 through Figure 36.

Table 45. JTAG AC Timing Specifications (Independent of SYS_CLK_IN)[1]

At recommended operating conditions (see Table 2).

Parameter	Symbol[2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t_{JTKHKL}	11	—	ns	—
JTAG external clock rise and fall times	t_{JTGR}, t_{JTGF}	0	2	ns	—
$\overline{\text{TRST}}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	 t_{JTDVKH} t_{JTIVKH}	 4 4	 — —	ns	4
Input hold times: Boundary-scan data TMS, TDI	 t_{JTDXKH} t_{JTIXKH}	 10 10	 — —	ns	4
Valid times: Boundary-scan data TDO	 t_{JTKLDV} t_{JTKLOV}	 2 2	 15 15	ns	5

Table 45. JTAG AC Timing Specifications (Independent of SYS_CLK_IN)[1] (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol[2]	Min	Max	Unit	Notes
Output hold times: Boundary-scan data TDO	 t_{JTKLDX} t_{JTKLOX}	 2 2	 — —	ns	 5
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	 5, 6 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 32). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design and characterization.

The following figure provides the AC test load for TDO and the boundary-scan outputs of the MPC8306S.

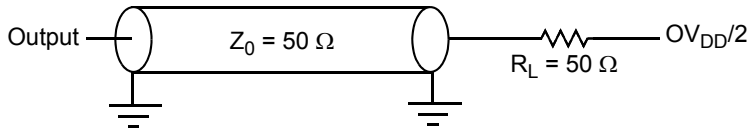


Figure 32. AC Test Load for the JTAG Interface

The following figure provides the JTAG clock input timing diagram.

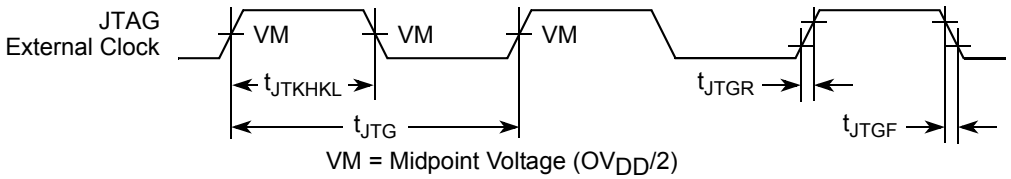


Figure 33. JTAG Clock Input Timing Diagram

The following figure provides the $\overline{\text{TRST}}$ timing diagram.

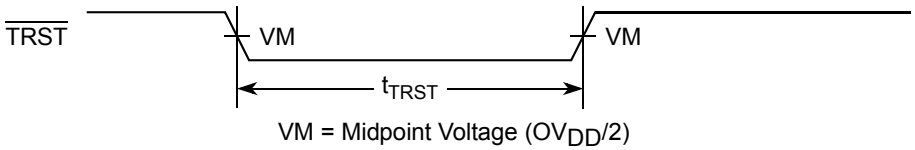


Figure 34. $\overline{\text{TRST}}$ Timing Diagram

19 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8306S is available in a thermally enhanced MAPBGA (mold array process-ball grid array); see Section 19.1, "Package Parameters for the MPC8306S," and Section 19.2, "Mechanical Dimensions of the MPC8306S MAPBGA," for information on the MAPBGA.

19.1 Package Parameters for the MPC8306S

The package parameters are as provided in the following list.

Package outline	19 mm × 19 mm
Package Type	MAPBGA
Interconnects	369
Pitch	0.80 mm
Module height (typical)	1.48 mm; Min = 1.31mm and Max 1.61mm
Solder Balls	96 Sn / 3.5 Ag / 0.5 Cu (VM package)
Ball diameter (typical)	0.40 mm

19.2 Mechanical Dimensions of the MPC8306S MAPBGA

The following figure shows the mechanical dimensions and bottom surface nomenclature of the MPC8306S, 369-MAPBGA package.

Table 46. MPC8306S Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MEMC_MA[8]	T1	O	GV_{DD}	—
MEMC_MA[9]	P4	O	GV_{DD}	—
MEMC_MA[10]	L4	O	GV_{DD}	—
MEMC_MA[11]	T2	O	GV_{DD}	—
MEMC_MA[12]	U1	O	GV_{DD}	—
MEMC_MA[13]	U2	O	GV_{DD}	—
MEMC_MWE_B	K1	O	GV_{DD}	—
MEMC_MRAS_B	K2	O	GV_{DD}	—
MEMC_MCAS_B	J1	O	GV_{DD}	—
MEMC_MCS_B[0]	J4	O	GV_{DD}	—
MEMC_MCS_B[1]	H1	O	GV_{DD}	—
MEMC_MCKE[0]	U4	O	GV_{DD}	—
MEMC_MCK[0]	V1	O	GV_{DD}	—
MEMC_MCK_B[0]	W1	O	GV_{DD}	—
MEMC_MODT[0]	H2	O	GV_{DD}	—
MEMC_MODT[1]	H4	O	GV_{DD}	—
MEMC_MVREF	L8		GV_{DD}	—
Local Bus Controller Interface				
LAD[0]	B7	IO	OV_{DD}	—
LAD[1]	D9	IO	OV_{DD}	—
LAD[2]	A6	IO	OV_{DD}	—
LAD[3]	B8	IO	OV_{DD}	—
LAD[4]	A7	IO	OV_{DD}	—
LAD[5]	A8	IO	OV_{DD}	—
LAD[6]	A9	IO	OV_{DD}	—
LAD[7]	D10	IO	OV_{DD}	—
LAD[8]	B10	IO	OV_{DD}	—
LAD[9]	A10	IO	OV_{DD}	—
LAD[10]	B11	IO	OV_{DD}	—
LAD[11]	D12	IO	OV_{DD}	—
LAD[12]	D11	IO	OV_{DD}	—
LAD[13]	A11	IO	OV_{DD}	—
LAD[14]	A12	IO	OV_{DD}	—
LAD[15]	B13	IO	OV_{DD}	—
LA[16]	A13	IO	OV_{DD}	—

Table 46. MPC8306S Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Clock Interface				
QE_CLK_IN	P23	I	OV_{DD}	—
SYS_CLK_IN	R23	I	OV_{DD}	—
RTC_PIT_CLOCK	V23	I	OV_{DD}	—
Miscellaneous Signals				
QUIESCE_B	A2	O	OV_{DD}	—
THERM0	D6	I	OV_{DD}	—
GPIO				
GPIO[0]/MSRCID0 (DDR ID)	E5	IO	OV_{DD}	—
GPIO[1]/MSRCID1 (DDR ID)	E6	IO	OV_{DD}	—
GPIO[2]/MSRCID2 (DDR ID)	D4	IO	OV_{DD}	—
GPIO[3]/MSRCID3 (DDR ID)	C2	IO	OV_{DD}	—
GPIO[4]/MSRCID4 (DDR ID)	C1	IO	OV_{DD}	—
GPIO[5]/MDVAL (DDR ID)	B1	IO	OV_{DD}	—
GPIO[6]/QE_EXT_REQ_3	B3	IO	OV_{DD}	—
GPIO[7]/QE_EXT_REQ_1	B2	IO	OV_{DD}	—
USB				
USBDR_PWRFAULT/IIC_SDA2/CE_PIO_1	AC4	IO	OV_{DD}	2
USBDR_CLK/UART2_SIN[2]/UART2_CTS_B[1]	Y9	I	OV_{DD}	
USBDR_DIR/IIC_SCL2	AC3	IO	OV_{DD}	2
USBDR_NXT/UART2_SIN[1]/QE_EXT_REQ_4	AC2	IO	OV_{DD}	—
USBDR_PCTL[0]/UART2_SOUT[1]/ LB_POR_CFG_BOOT_ECC	AB3	IO	OV_{DD}	—
USBDR_PCTL[1]/UART2_SOUT[2]/ UART2_RTS_B1/LB_POR_BOOT_ERR	Y8	O	OV_{DD}	—
USBDR_STP/QE_EXT_REQ_2	W6	IO	OV_{DD}	—
USBDR_TXDRXD[0]/UART1_SOUT[1]/ GPIO[32]/QE_TRB_O	AB7	IO	OV_{DD}	—
USBDR_TXDRXD[1]/UART1_SIN[1]/GPIO[33]/ QE_TRB_I	AB8	IO	OV_{DD}	—
USBDR_TXDRXD[2]/UART1_SOUT[2]/ UART1_RTS_B1/QE_BRG[1]	AC6	IO	OV_{DD}	—
USBDR_TXDRXD[3]/UART1_SIN[2]/ UART1_CTS_B1/QE_BRG[2]	AC5	IO	OV_{DD}	—
USBDR_TXDRXD[4]/GPIO[34]/QE_BRG[3]	AB5	IO	OV_{DD}	—
USBDR_TXDRXD[5]/GPIO[35]/QE_BRG[4]	Y7	IO	OV_{DD}	—
USBDR_TXDRXD[6]/GPIO[36]/QE_BRG[9]	Y6	IO	OV_{DD}	—

Table 46. MPC8306S Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
FEC1_TX_ER/GTM1_TOUT[4]_B/GPIO[27]	AC17	IO	OV_{DD}	—
FEC1_TXD0/GTM1_TOUT[1]_B/GPIO[28]	AB16	IO	OV_{DD}	—
FEC1_TXD1/GTM1_TOUT[2]_B/GPIO[29]	AC16	IO	OV_{DD}	—
FEC1_TXD2/GTM1_TOUT[3]_B/GPIO[30]	AC15	IO	OV_{DD}	—
FEC1_TXD3/GPIO[31]	AB14	IO	OV_{DD}	—
FEC2/GPIO				
FEC2_COL/GPIO[32]	AC14	IO	OV_{DD}	—
FEC2_CRS/GPIO[33]	AB13	IO	OV_{DD}	—
FEC2_RX_CLK/GPIO[34]	Y14	IO	OV_{DD}	—
FEC2_RX_DV/GPIO[35]	AC13	IO	OV_{DD}	—
FEC2_RX_ER/GPIO[36]	Y13	IO	OV_{DD}	—
FEC2_RXD0/GPIO[37]	AC12	IO	OV_{DD}	—
FEC2_RXD1/GPIO[38]	AB11	IO	OV_{DD}	—
FEC2_RXD2/GPIO[39]	AC11	IO	OV_{DD}	—
FEC2_RXD3/GPIO[40]	AB10	IO	OV_{DD}	—
FEC2_TX_CLK/GPIO[41]	Y12	IO	OV_{DD}	—
FEC2_TX_EN/GPIO[42]	AC10	IO	OV_{DD}	—
FEC2_TX_ER/GPIO[43]	AC9	IO	OV_{DD}	—
FEC2_TXD0/GPIO[44]	AC8	IO	OV_{DD}	—
FEC2_TXD1/GPIO[45]	Y11	IO	OV_{DD}	—
FEC2_TXD2/GPIO[46]	AC7	IO	OV_{DD}	—
FEC2_TXD3/GPIO[47]	Y10	IO	OV_{DD}	—
FEC3/GPIO				
FEC3_COL/GPIO[48]	J23	IO	OV_{DD}	—
FEC3_CRS/GPIO[49]	K23	IO	OV_{DD}	—
FEC3_RX_CLK/GPIO[50]	M20	IO	OV_{DD}	—
FEC3_RX_DV/FEC1_TMR_TX_ESFD/GPIO[51]	K22	IO	OV_{DD}	—
FEC3_RX_ER/FEC1_TMR_RX_ESFD/GPIO[52]	L22	IO	OV_{DD}	—
FEC3_RXD0/FEC2_TMR_TX_ESFD/GPIO[53]	L23	IO	OV_{DD}	—
FEC3_RXD1/FEC2_TMR_RX_ESFD/GPIO[54]	M23	IO	OV_{DD}	—
FEC3_RXD2/TSEC_TMR_TRIG1/GPIO[55]	N22	IO	OV_{DD}	—
FEC3_RXD3/TSEC_TMR_TRIG2/GPIO[56]	N23	IO	OV_{DD}	—
FEC3_TX_CLK/TSEC_TMR_CLK/GPIO[57]	N20	IO	OV_{DD}	—
FEC3_TX_EN/TSEC_TMR_GCLK/GPIO[58]	P20	IO	OV_{DD}	—
FEC3_TX_ER/TSEC_TMR_PP1/GPIO[59]	P22	IO	OV_{DD}	—

Table 52. QUICC Engine PLL Multiplication Factors (continued)

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF)
00111	0	× 7
01000	0	× 8
01001–11111	0	Reserved

The RCWL[CEVCOD] denotes the QUICC Engine PLL VCO internal frequency as shown in the following table.

Table 53. QUICC Engine PLL VCO Divider

RCWL[CEVCOD]	VCO Divider
00	2
01	4
10	8
11	Reserved

NOTE

The VCO divider (RCWL[CEVCOD]) must be set properly so that the QUICC Engine VCO frequency is in the range of 300–600 MHz. The QUICC Engine frequency is not restricted by the CSB and core frequencies. The CSB, core, and QUICC Engine frequencies should be selected according to the performance requirements.

The QUICC Engine VCO frequency is derived from the following equations:

qe_clk = (primary clock input × CEPMF) ÷ (1 + CEPDF)

QUICC Engine VCO Frequency = *qe_clk* × VCO divider × (1 + CEPDF)

20.5 Suggested PLL Configurations

To simplify the PLL configurations, the MPC8306S might be separated into two clock domains. The first domain contains the CSB PLL and the core PLL. The core PLL is connected serially to the CSB PLL, and has the csb_clk as its input clock. The second clock domain has the QUICC Engine PLL. The clock domains are independent, and each of their PLLs is configured separately.

The following table shows suggested PLL configurations for 33 and 66 MHz input clocks.

21 Thermal

This section describes the thermal specifications of the MPC8306S.

21.1 Thermal Characteristics

The following table provides the package thermal characteristics for the 369, 19 × 19 mm MAPBGA of the MPC8306S.

Table 55. Package Thermal Characteristics for MAPBGA

Characteristic	Board type	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection	Single-layer board (1s)	$R_{\theta JA}$	39	°C/W	1, 2
Junction-to-ambient natural convection	Four-layer board (2s2p)	$R_{\theta JA}$	24	°C/W	1, 2, 3
Junction-to-ambient (@200 ft/min)	Single-layer board (1s)	$R_{\theta JMA}$	32	°C/W	1, 3
Junction-to-ambient (@200 ft/min)	Four-layer board (2s2p)	$R_{\theta JMA}$	21	°C/W	1, 3
Junction-to-board	—	$R_{\theta JB}$	14	°C/W	4
Junction-to-case	—	$R_{\theta JC}$	9	°C/W	5
Junction-to-package top	Natural convection	Ψ_{JT}	2	°C/W	6

Notes:
1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.
3. Per JEDEC JESD51-6 with the board horizontal.
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

21.1.1 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$, where $P_{I/O}$ is the power dissipation of the I/O drivers.

21.1.2 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D) \qquad \textit{Eqn. 1}$$

where:

T_J = junction temperature (°C)

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. As a general statement, the value obtained on a single layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

21.1.3 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_B + (R_{\theta JB} \times P_D) \qquad \textit{Eqn. 2}$$

where:

T_J = junction temperature (°C)

T_B = board temperature at the package perimeter (°C)

$R_{\theta JB}$ = junction-to-board thermal resistance (°C/W) per JESD51-8

P_D = power dissipation in package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

21.1.4 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, the thermal characterization parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D) \qquad \textit{Eqn. 3}$$

where:

T_J = junction temperature (°C)

lifetime of the package. Recommended maximum force on the top of the package is 10 lb (4.5 kg) force. If an adhesive attachment is planned, the adhesive should be intended for attachment to painted or plastic surfaces and its performance verified under the application requirements.

21.2.1 Experimental Determination of the Junction Temperature with a Heat Sink

When heat sink is used, the junction temperature is determined from a thermocouple inserted at the interface between the case of the package and the interface material. A clearance slot or hole is normally required in the heat sink. Minimizing the size of the clearance is important to minimize the change in thermal performance caused by removing part of the thermal interface to the heat sink. Because of the experimental difficulties with this technique, many engineers measure the heat sink temperature and then back calculate the case temperature using a separate measurement of the thermal resistance of the interface.

From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance using the following equation:

$$T_J = T_C + (R_{\theta JC} \times P_D) \qquad \textit{Eqn. 5}$$

where:

T_C = case temperature of the package (°C)
$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)
P_D = power dissipation (W)

22 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8306S.

22.1 System Clocking

The MPC8306S includes three PLLs.

- The system PLL (AV_{DD2}) generates the system clock from the externally supplied SYS_CLK_IN input. The frequency ratio between the system and SYS_CLK_IN is selected using the system PLL ratio configuration bits as described in Section 20.2, “System PLL Configuration.”
- The e300 core PLL (AV_{DD3}) generates the core clock as a slave to the system clock. The frequency ratio between the e300 core clock and the system clock is selected using the e300 PLL ratio configuration bits as described in Section 20.3, “Core PLL Configuration.”
- The QUICC Engine PLL (AV_{DD1}) which uses the same reference as the system PLL. The QUICC Engine block generates or uses external sources for all required serial interface clocks.

24 Document Revision History

The following table provides a revision history for this document.

Table 59. Document Revision History

Rev. No.	Date	Substantive Change(s)
1	09/2011	• Added Power numbers for core frequency of 333 MHz in Table 5. • Updated QUICC Engine frequency in Table 5. • Added SPISEL_BOOT in MPC8306 Pin out Listing Table 46. • Corrected SPISEL Pin Type in Table 46 • Updated QUICC Engine frequency from 200 MHz to 233 MHz in Table 48. • Added new PLL configurations as per new core frequency in Table 54. • Updated CEPMF and CEDF as per new QE frequency in Table 54. • Added AF to indicate 333 MHz in Table 57 • Updated QE Frequency to 233 MHz in Table 57.
0	03/2011	Initial Release